



SiC SCHOTTKY DIODE TYPE 2×70A

Features

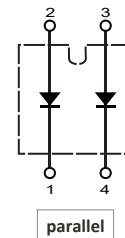
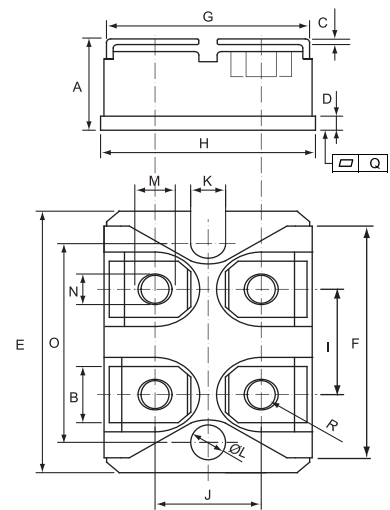
- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Isolation type package
- Temperature independent switching behavior
- VDC 1200 V
- I_F (T_C<135°C) 2×70 A

Benefits

- Unipolar rectifier
- Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices without thermal runaway

Applications

- Motor drives
- Switch mode power supplies
- Ev chargers
- Solar inverters
- Welding equipment
- Power factor correction
- Diode snubber
- Automotive
- Induction heating



Maximum Ratings

Operating Junction Temperature : - 55 °C to +175 °C
 Storage Temperature : - 55 °C to +175 °C

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum DC Blocking Voltage
CSRI2×70-120	1200V	1200V

Maximum Rating	Symbol	Conditions	Value	Unit
Continuous forward current (per diode)	I _F	T _C =135 °C	70	A
Surge non-repetitive forward current sine halfwave (per diode)	I _{FSM}	T _C =25 °C, t _p =8.3 ms	600	
		T _C =150 °C, t _p =8.3 ms	375	
Non-repetitive peak forward current (per diode)	I _{F,max}	T _C =25 °C, t _p =10 μs	2400	
		T _C =150 °C, t _p =10 μs	1500	
Repetitive peak reverse voltage	V _{RRM}	T _J =25 °C	1200	V
Isolation voltage (between Terminals and Baseplate)	V _{iso}	50/60 Hz, t=1min I _{ISOL} ≤ 1mA	2500	V
Mounting torque	M _d	To heatsink	1.3	Nm
		To terminal	1.1	

	DIMENSIONS			
	INCHES		MM	
	MIN	MAX	MIN	MAX
A	0.460	0.483	11.68	12.28
B	0.307	0.323	7.80	8.20
C	0.030	0.033	0.75	0.85
D	0.071	0.081	1.80	2.05
E	1.488	1.504	37.80	38.20
F	1.248	1.260	31.70	32.00
G	0.917	0.957	23.30	24.30
H	0.996	1.008	25.30	25.60
I	0.579	0.602	14.70	15.30
J	0.492	0.516	12.50	13.10
K	0.161	0.169	4.10	4.30
L	0.161	0.169	4.10	4.30
M	0.181	0.197	4.60	5.00
N	0.165	0.181	4.20	4.60
O	1.181	1.197	30.00	30.40
Q	-0.002	0.004	-0.05	0.10
R	M4*8			



Electrical Characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified. (per diode)

Static Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V_{DC}		1,200	-	-	V
Diode forward voltage	V_F	$I_F=70\text{A}, T_j=25\text{ }^\circ\text{C}$	-	1.6	1.8	V
		$I_F=70\text{A}, T_j=175\text{ }^\circ\text{C}$	-	2.4	2.9	
Reverse current	I_R	$V_R=1,200\text{V}, T_j=25\text{ }^\circ\text{C}$	-	3.6	181	μA
		$V_R=1,200\text{V}, T_j=175\text{ }^\circ\text{C}$	-	230	2,300	

AC Characteristics (per diode)

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Total capacitive charge	Q_{rr}	$V_R=1,200\text{V}, T_j=25\text{ }^\circ\text{C}$	-	205	-	nC
Total capacitance	C	$V_R=0\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	3,300	-	pF
		$V_R=600\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	240	-	
		$V_R=1,000\text{V}, f=1\text{ MHz}$ $T_j=25\text{ }^\circ\text{C}$	-	230	-	

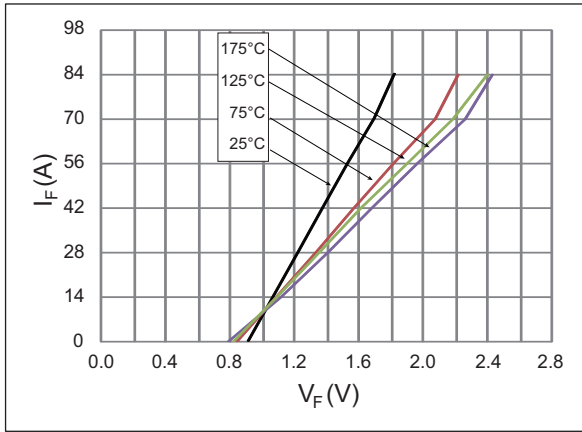
Thermal Characteristics (per diode)

Characteristics	Symbol	Values	Unit
		typ.	
Thermal resistance from junction to case	$R_{\theta JC}$	0.34	$^\circ\text{C/W}$

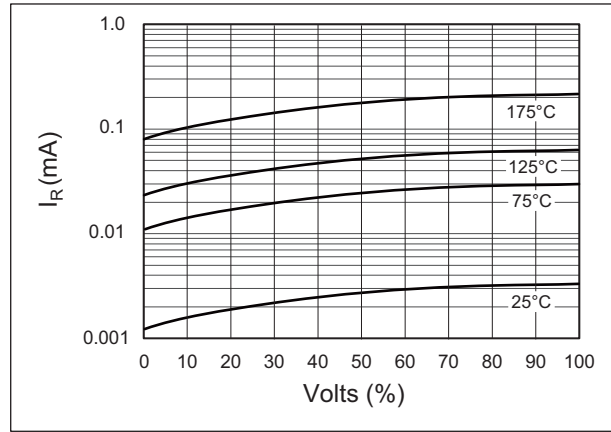


Typical Performance

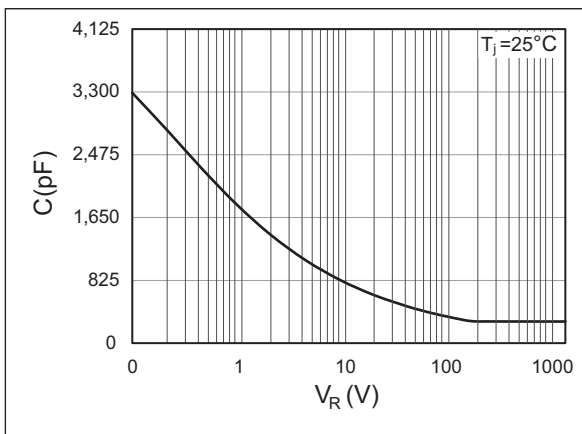
Forward Characteristics (parameterized on T_j)



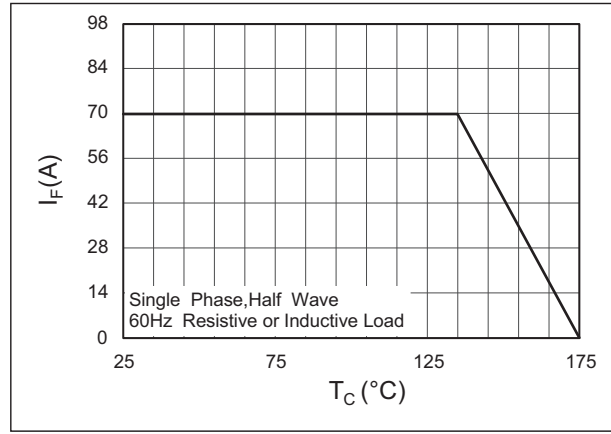
Reverse Characteristics (parameterized on T_j)



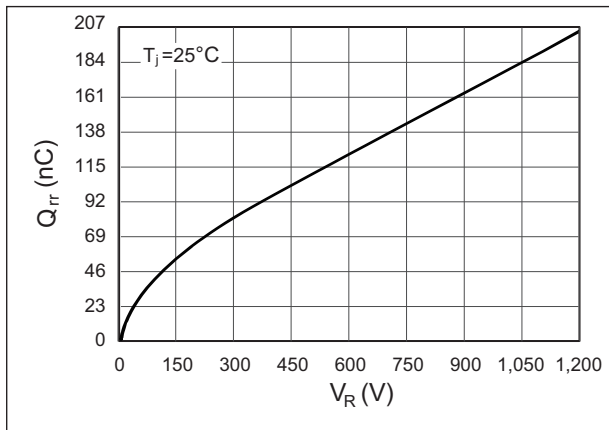
Capacitance



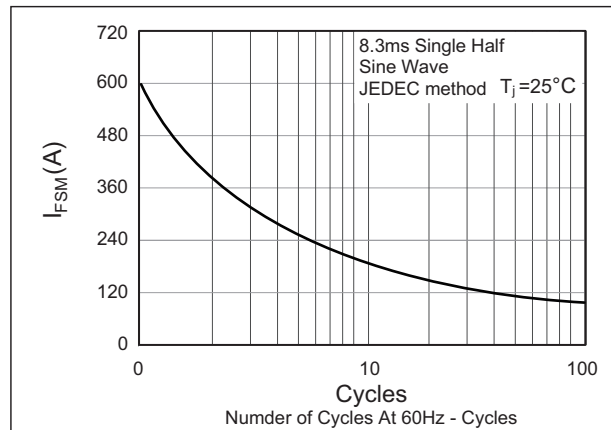
Current Derating



Recovery Charge



Forward Surge Current





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